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**(54) METHOD OF HEAT-TREATING SEMICONDUCTOR WAFER**

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of heat-treating semiconductor wafer by which a semiconductor wafer which is an object to be treated can be heat-treated without breakage.

SOLUTION: In this method of the heat-treating semiconductor wafer, the semiconductor wafer is heat-treated by means of a flash light radiating means constituted of a flashing light radiating lamp after the wafer is preheated to a prescribed temperature by means of a preheating means. The preheating temperature is controlled so that a maximum tensile stress of the semiconductor wafer may not reach a threshold tensile stress of the wafer itself when the wafer is heated by means of the flashing light radiating lamp.

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